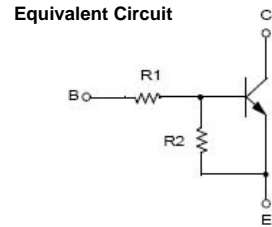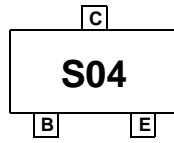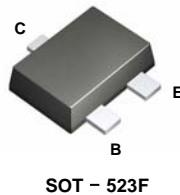**FAIRCHILD**

SEMICONDUCTOR®

July 2007

FJY3004R
NPN Epitaxial Silicon Transistor

Features

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R1=47KΩ, R2=47KΩ)
- Complement to FJY4004R

SOT − 523F

S04

Equivalent Circuit

Absolute Maximum Ratings * T_a = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current	100	mA
T_{STG}	Storage Temperature Range	-55~150	°C
T_J	Junction Temperature	150	°C
P_C	Collector Power Dissipation, by $R_{\theta JA}$	200	mW

* These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

Thermal Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	600	°C/W

* Minimum land pad size.

Electrical Characteristics* T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Typ	MAX	Units
$V_{(BR)CBO}$	Collector-Emitter Breakdown Voltage	I_C = 10 uA, I_E = 0	50			V
$V_{(BR)CEO}$	Collector-Base Breakdown Voltage	I_C = 100 uA, I_B = 0	50			V
I_{CBO}	Collector-Cutoff Current	V_{CB} = 40 V, I_E = 0			0.1	uA
h_{FE}	DC Current Gain	V_{CE} = 5 V, I_C = 5 mA	56			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 0.5 mA			0.3	V
f_T	Current Gain - Bandwidth Product	V_{CE} = 10V, I_C = 5 mA		250		MHz
C_{cb}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 1.0 MHz		3.7		pF
$V_{I(off)}$	Input Off Voltage	V_{CE} = 5 V, I_C = 100uA	0.5			V
$V_{I(on)}$	Input On Voltage	V_{CE} = 0.3V, I_C = 2mA			3	V
R_1	Input Resistor		32	47	62	KΩ
R_1/R_2	Resistor Ratio		0.9	1.0	1.1	

* Pulse Test: PW≤300μs, Duty Cycle≤2%

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Typical Performance Characteristics

Figure 1. DC current Gain

V_{CE} = 5V
R_1 = 47K
R_2 = 47K

h_{FE}, DC CURRENT GAIN

I_C[mA], COLLECTOR CURRENT
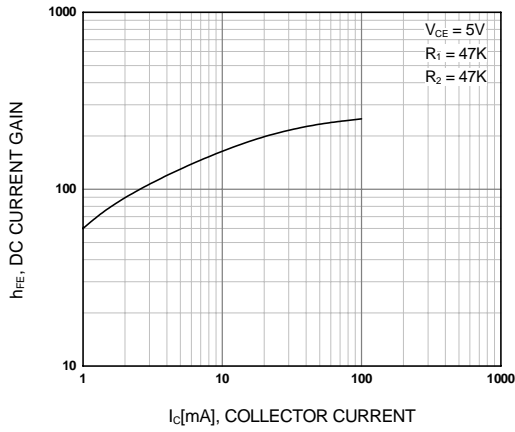
Figure 2. Input On Voltage

V_{CE} =0.3V
R_1 = 47 K
R_2 = 47 K

V_i(on)[V], INPUT VOLTAGE

I_C[mA], COLLECTOR CURRENT
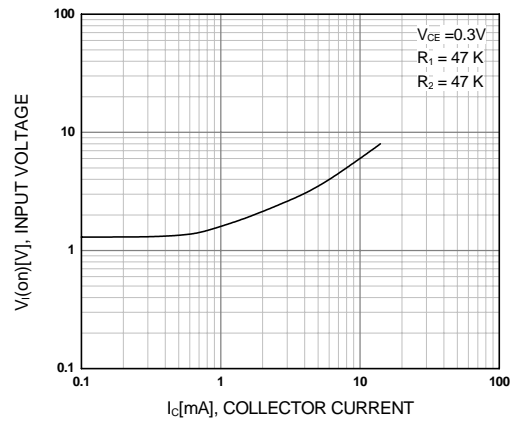
Figure 3. Input off Voltage

V_{CE} = 5V
R_1 = 47K
R_2 = 47K

I_C [μA], COLLECTOR CURRENT

V_i(off)[V], INPUT OFF VOLTAGE
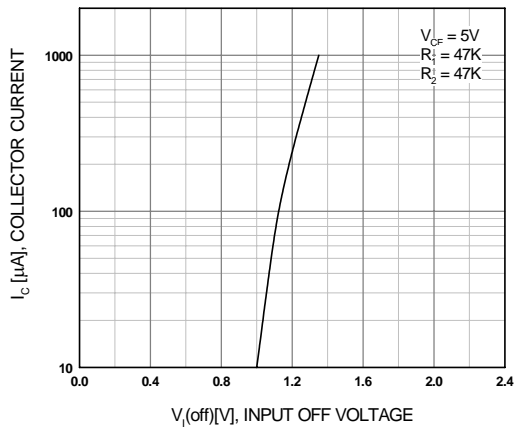
Figure 4. Power Derating

P_C[mW], POWER DISSIPATION

T_a[°C], AMBIENT TEMPERATURE
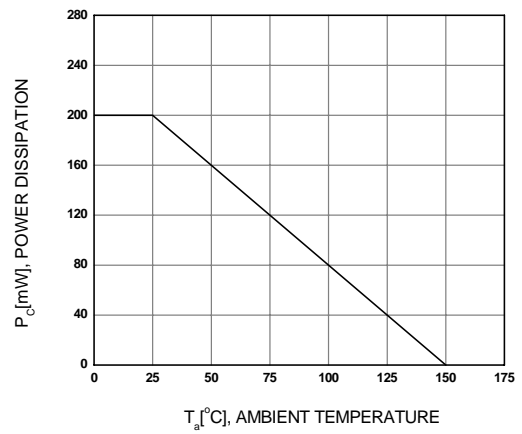
Package Dimensions

SOT-523F

1.70
1.50

0.35
0.25

3

0.98
0.78

1.70
1.50

1

2

(0.15)

0.50

1.00

0.50

0.50

0.50

1.14

1.80

0.50

0.66

LAND PATTERN RECOMMENDATION

0.78
0.58

SEE DETAIL A

0.20
0.04

0.43
0.28

0.54
0.34

NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE CONFORMS TO EIAJ
   SC89 PACKAGING STANDARD.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE EXCLUSIVE OF BURRS,
   MOLD FLASH, AND TIE BAR EXTRUSIONS.

DETAIL A
SCALE 2 : 1

0.10
0.00

Dimensions in Millimeters

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FASTr™	PDP-SPM™	SuperSOT™-8	
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